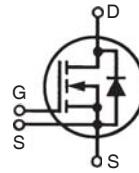
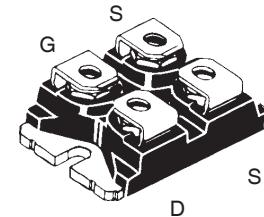


**X-Class HiPerFET™
Power MOSFET**
IXFN52N100X
**N-Channel Enhancement Mode
Avalanche Rated**

 **V_{DSS} = 1000V
 I_{D25} = 44A
 $R_{DS(on)}$ ≤ 125mΩ**
**miniBLOC, SOT-227
E153432**

**G = Gate D = Drain
S = Source**

Symbol	Test Conditions	Maximum Ratings		
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	1000	V	
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GS} = 1\text{M}\Omega$	1000	V	
V_{GSS}	Continuous	± 30	V	
V_{GSM}	Transient	± 40	V	
I_{D25}	$T_C = 25^\circ\text{C}$	44	A	
I_{DM}	$T_C = 25^\circ\text{C}$, Pulse Width Limited by T_{JM}	100	A	
I_A	$T_C = 25^\circ\text{C}$	10	A	
E_{AS}	$T_C = 25^\circ\text{C}$	3	J	
P_D	$T_C = 25^\circ\text{C}$	830	W	
dv/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$	15	V/ns	
T_J		-55 ... +150	°C	
T_{JM}		150	°C	
T_{stg}		-55 ... +150	°C	
V_{ISOL}	50/60 Hz, RMS	2500	V~	
	$I_{ISOL} \leq 1\text{mA}$	3000	V~	
M_d	Mounting Torque	1.5/13	Nm/lb.in	
	Terminal Connection Torque	1.3/11.5	Nm/lb.in	
Weight		30	g	

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0\text{V}$, $I_D = 1\text{mA}$	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4\text{mA}$	3.5		6.0 V
I_{GSS}	$V_{GS} = \pm 30\text{V}$, $V_{DS} = 0\text{V}$		± 100	nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0\text{V}$ $T_J = 125^\circ\text{C}$		50 μA 5 mA	
$R_{DS(on)}$	$V_{GS} = 10\text{V}$, $I_D = 26\text{A}$, Note 1		125 mΩ	

Features

- International Standard Package
- miniBLOC, with Aluminium Nitride Isolation
- Isolation Voltage 2500 V~
- Low Q_G
- Avalanche Rated
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

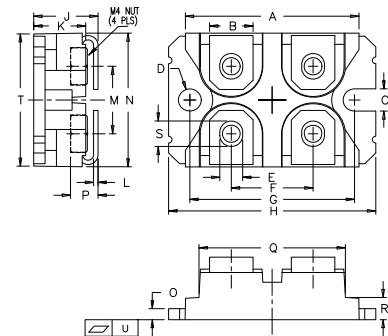
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
g_{fs}	$V_{DS} = 20\text{V}$, $I_D = 26\text{A}$, Note 1	23	37	S
R_{Gi}	Gate Input Resistance		0.5	Ω
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$	6725		pF
C_{oss}		1620		pF
C_{rss}		123		pF
Effective Output Capacitance				
$C_{o(er)}$	Energy related } $V_{GS} = 0\text{V}$	220		pF
$C_{o(tr)}$	Time related } $V_{DS} = 0.8 \cdot V_{DSS}$	1070		pF
$t_{d(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 26\text{A}$ $R_G = 1\Omega$ (External)	34		ns
t_r		13		ns
$t_{d(off)}$		107		ns
t_f		9		ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 26\text{A}$	245		nC
Q_{gs}		53		nC
Q_{gd}		125		nC
R_{thJC}			0.15	$^\circ\text{C}/\text{W}$
R_{thCS}		0.10		$^\circ\text{C}/\text{W}$

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_s	$V_{GS} = 0\text{V}$		52	A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}		208	A
V_{SD}	$I_F = I_s$, $V_{GS} = 0\text{V}$, Note 1		1.4	V
t_{rr}	$I_F = 26\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$, $V_{GS} = 0\text{V}$	260		ns
Q_{RM}		2.7		μC
I_{RM}		20.8		A

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

SOT-227B (IXFN) Outline



(M4 screws (4x) supplied)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	.76	.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2 4,860,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2 4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

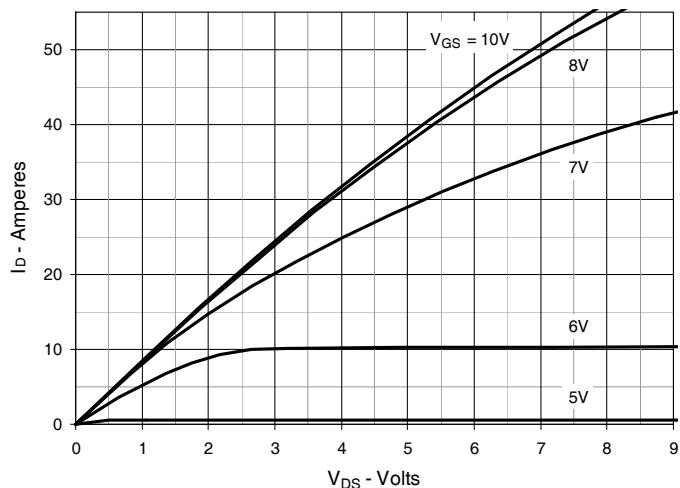
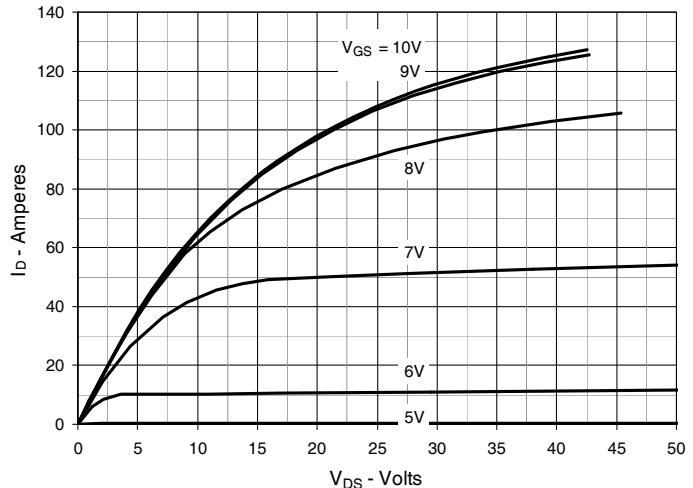
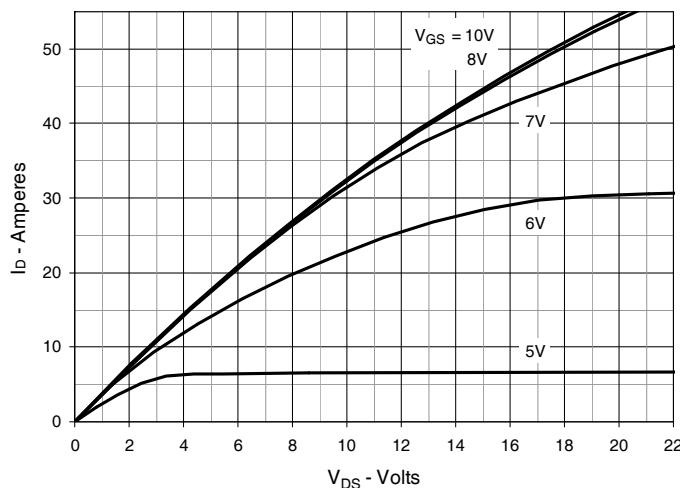
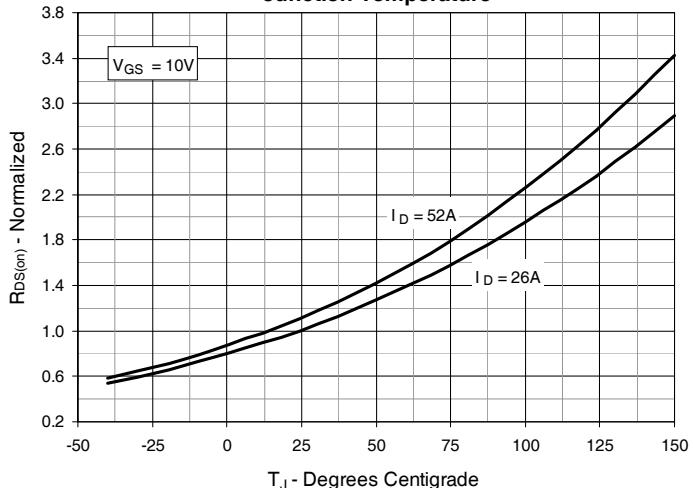
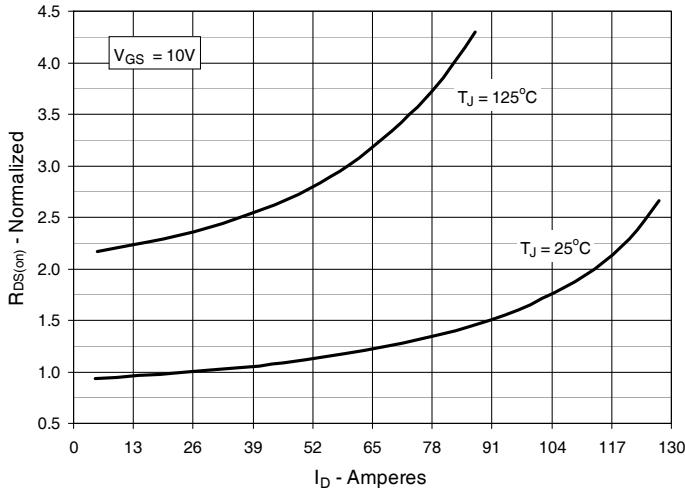
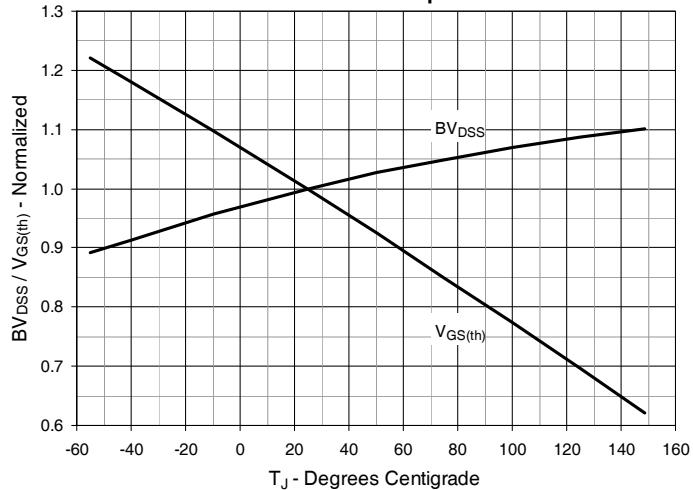
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 26\text{A}$ Value vs. Junction Temperature

Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 26\text{A}$ Value vs. Drain Current

Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature


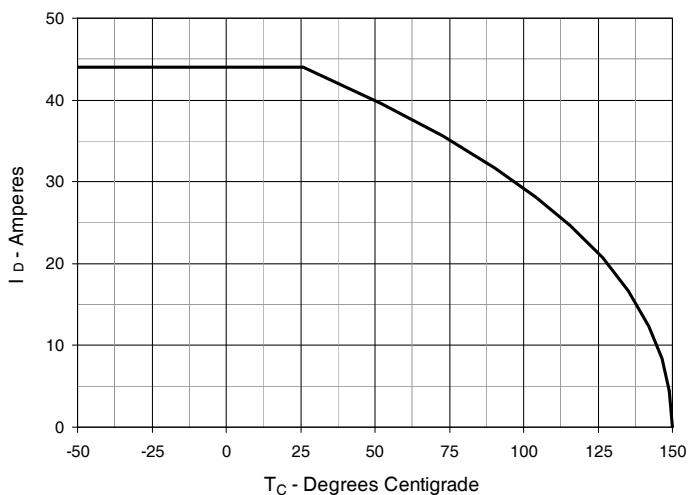
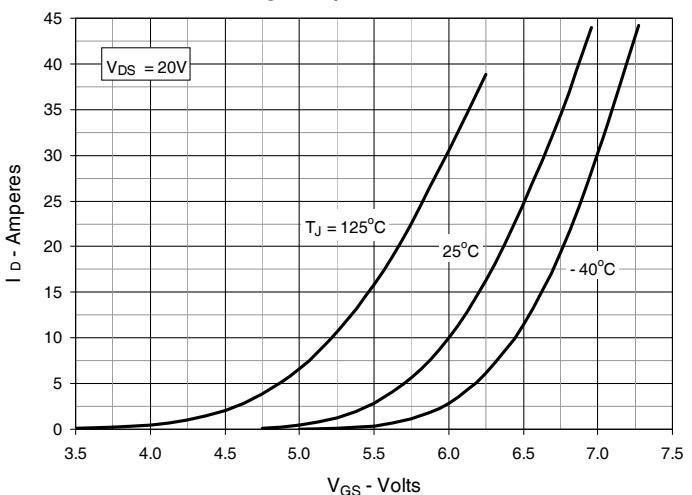
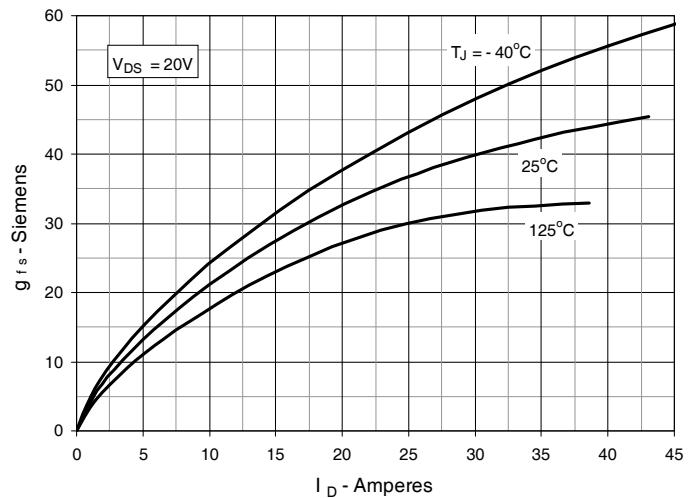
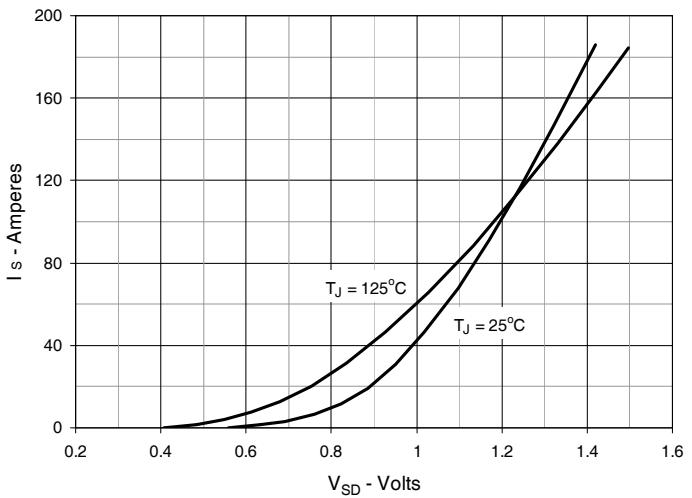
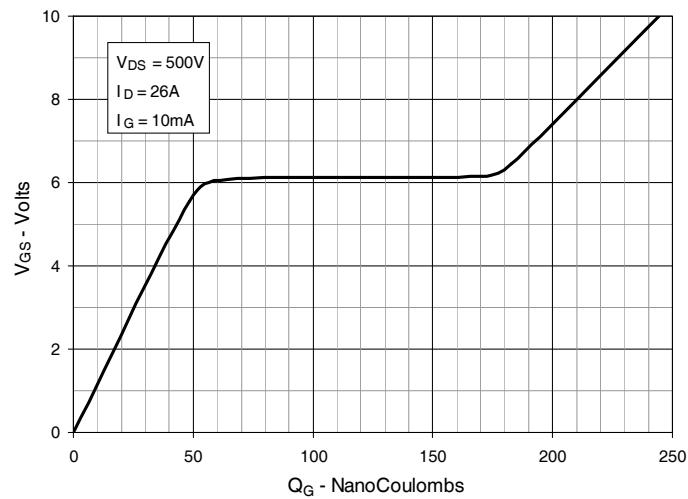
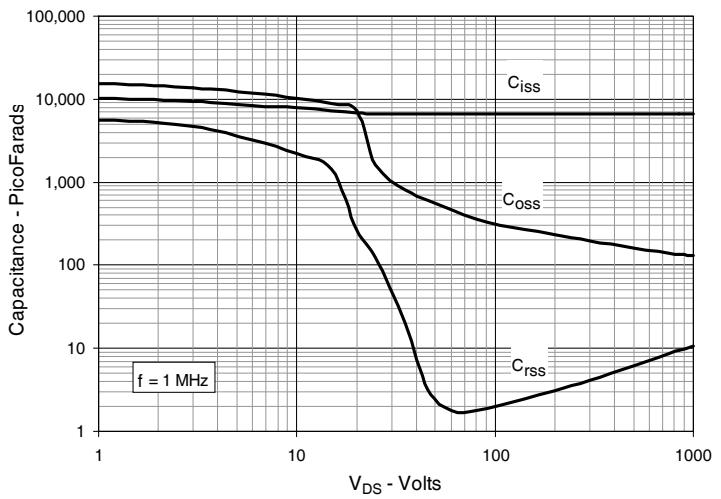
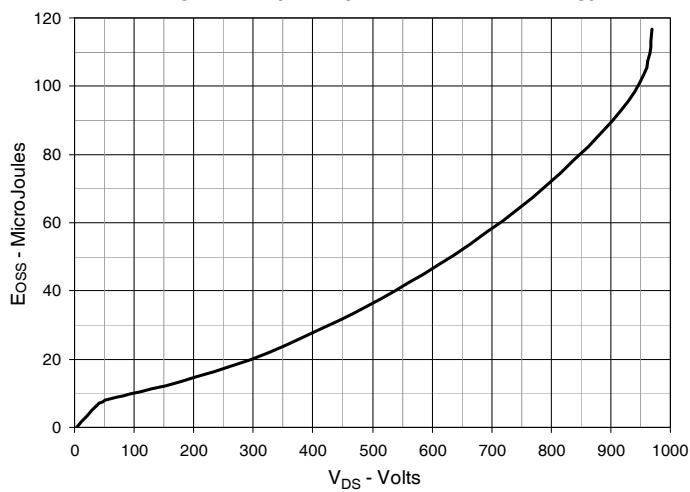
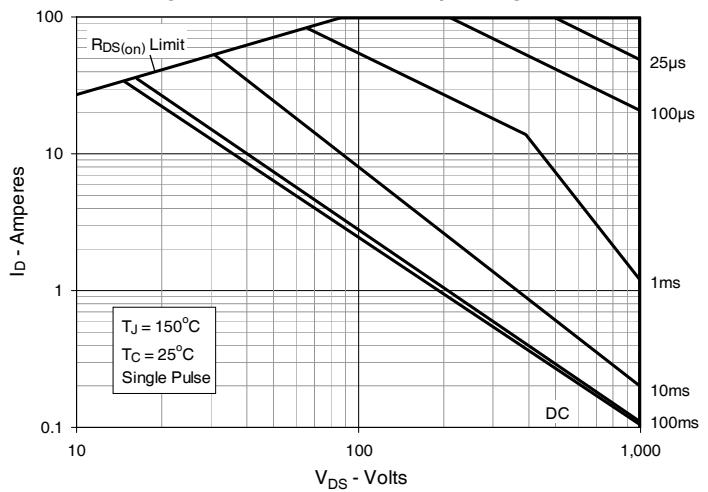
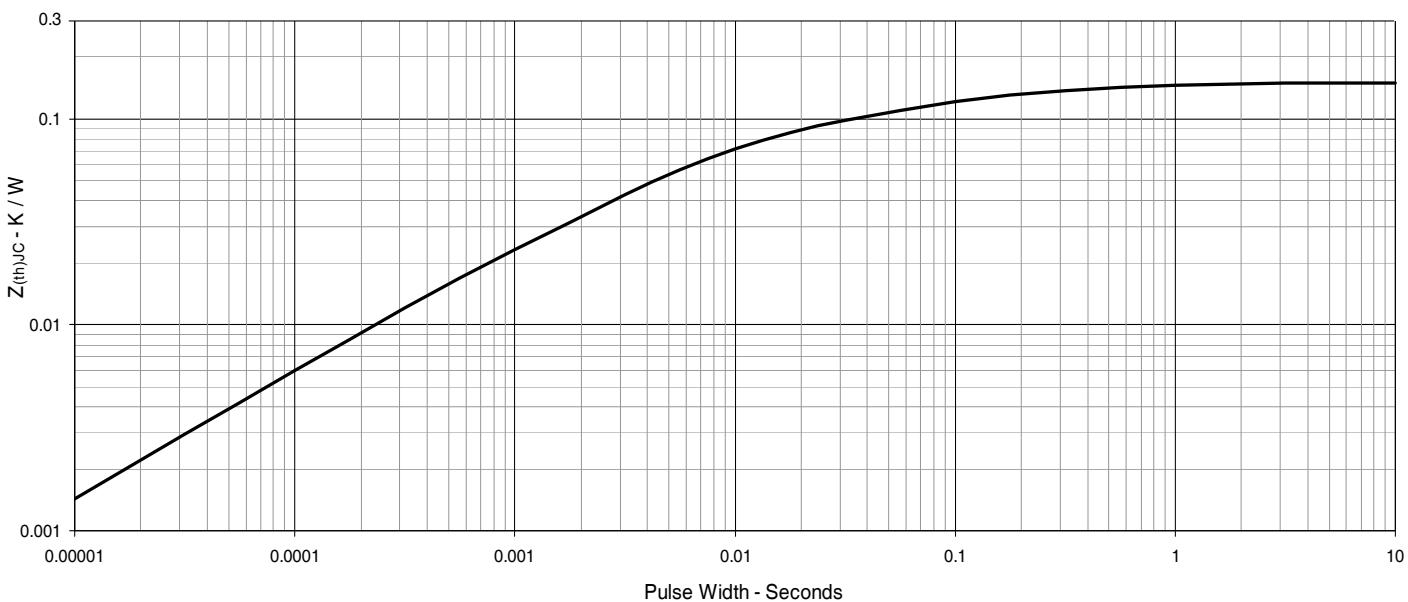
Fig. 7. Maximum Drain Current vs. Case Temperature**Fig. 8. Input Admittance****Fig. 9. Transconductance****Fig. 10. Forward Voltage Drop of Intrinsic Diode****Fig. 11. Gate Charge****Fig. 12. Capacitance**

Fig. 13. Output Capacitance Stored Energy**Fig. 14. Forward-Bias Safe Operating Area****Fig. 15. Maximum Transient Thermal Impedance**

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[T512F-YEB](#) [T513F](#) [T514F](#) [T554](#) [T612FSE](#) [25.161.3453.0](#) [25.179.2253.0](#) [25.194.3253.0](#) [25.325.1253.1](#) [25.326.4253.1](#) [25.330.0953.1](#)
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